

IN THE CLAIMS

Complete listing of the claims

1. (Currently amended) A film forming system comprising:

a chamber,
a precursory gas supplying line to supply the chamber with precursory gas,
a reactive gas supplying line to supply the chamber with reactive gas,
a precursory gas vaporizer for outputting precursory gas to the precursory gas supplying line,

a reactive gas vaporizer for outputting reactive gas to the reactive gas supplying line, and
a purge gas supplying line to supply purge gas that purges the precursory gas and the reactive gas, and that forms a thin film on a substrate in the chamber by supplying the precursory gas or the reactive gas and purging alternately,

wherein the precursory gas supplying line comprises a precursory gas middle line having a predetermined volume and into which the precursory gas can be filled at a time when the precursory gas is not supplied; ~~and/or wherein the reactive gas supplying line comprises a reactive gas middle line having a certain volume and into which the reactive gas can be filled at a time when the reactive gas is not supplied;~~

wherein a first switching valve is provided on the precursory gas supplying line ~~and/or reactive gas supplying line~~ at a position downstream of the precursory gas vaporizer ~~and/or the reactive gas vaporizer~~ at an inlet port of the precursory gas middle line ~~and/or the reactive gas middle line~~;

wherein a second switching valve is provided on the precursory gas supplying line ~~and/or reactive gas supplying line~~ at a position downstream of the first switching valve at an outlet port of the precursory gas middle line ~~and/or the reactive gas middle line~~; and

the chamber is provided downstream from the second switching valve.

2. (Cancelled)

3. (Previously presented) The film forming system described in claim 1, wherein the first switching valve or the second switching valve is a three-way valve.

4. (Currently amended) The film forming system described in claim 1, wherein the purge gas supplying line is connected to the precursory gas supplying line to which the precursory gas middle line is arranged ~~and/or the reactive gas supplying line to which the reactive gas middle line is arranged~~ and the precursory gas ~~and/or the reactive gas each of which is filled in the precursory gas middle line and/or the reactive gas middle line~~ is supplied to the chamber by pushing out the precursory gas ~~and/or the reactive gas~~ by the use of the purge gas.

5. (Currently amended) The film forming system described in claim 1, wherein the precursory gas ~~and/or the reactive gas~~ is supplied to the chamber in 0.1 through 2 second.

6. (Currently amended) The film forming system described in claim 1, wherein concentration adjusting devices to adjust ~~each~~ concentration of the precursory gas ~~and the reactive gas~~ is connected to the precursory gas supplying line ~~and the reactive gas supplying line respectively~~ and ~~each~~ ~~the~~ concentration adjusting device adjusts ~~each~~ ~~the~~ concentration of the precursory gas ~~and the reactive gas~~ so as to supply ~~each~~ ~~the~~ precursory gas at more than or equal to 0.15×10^{-6} mol/cm² with respect to an area of the substrate on which the thin film is formed.

7. (Currently amended) The film forming system described in claim 1, wherein ~~each~~ ~~of the~~ precursory gas supplying line ~~and the reactive gas supplying line~~ is independently connected to the chamber.

8. (Currently amended) The film forming system described in claim 1, and that is arranged to purge the chamber so that ~~each~~ concentration of the precursory gas ~~and/or the reactive gas~~ becomes less than or equal to 1/1000 in less than or equal to 2 seconds.

9. (Cancelled)

10. (New) A film forming system comprising:

a chamber,
a precursory gas supplying line to supply the chamber with precursory gas,
a reactive gas supplying line to supply the chamber with reactive gas,
a precursory gas vaporizer for outputting precursory gas to the precursory gas supplying line,
a reactive gas vaporizer for outputting reactive gas to the reactive gas supplying line, and
a purge gas supplying line to supply purge gas that purges the precursory gas and the reactive gas, and that forms a thin film on a substrate in the chamber by supplying the precursory gas or the reactive gas and purging alternately,
wherein the reactive gas supplying line comprises a reactive gas middle line having a certain volume and into which the reactive gas can be filled at a time when the reactive gas is not supplied,
wherein a first switching valve is provided on the reactive gas supplying line at a position downstream of the reactive gas vaporizer at an inlet port of the reactive gas middle line;
wherein a second switching valve is provided on the reactive gas supplying line at a position downstream of the first switching valve at an outlet port of the reactive gas middle line; and
the chamber is provided downstream from the second switching valve.